

Features

- Epitaxial Planar Die Construction
- Low Collector-Emitter Saturation Voltage
- Ideal for Low Power Amplification and Switching
- Complementary PNP Type Available (2DB1689)
- Ultra-Small Surface Mount Package
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green Device" (Note 2)



2DD2652

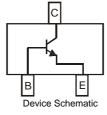
LOW V_{CE(SAT)} NPN SURFACE MOUNT TRANSISTOR

Mechanical Data

- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.006 grams (approximate)



Top View



Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	15	V
Collector-Emitter Voltage	V _{CEO}	12	V
Emitter-Base Voltage	V _{EBO}	6	V
Collector Current - Continuous	lc	1.5	А
Peak Pulse Collector Current	I _{CM}	3	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit
	Symbol	value	Unit
Power Dissipation (Note 3) @ $T_A = 25^{\circ}C$	PD	300	mW
Thermal Resistance, Junction to Ambient (Note 3) @ T _A = 25°C	$R_{ ext{ heta}JA}$	417	°C/W
Power Dissipation (Note 4) @ $T_A = 25^{\circ}C$	PD	500	mW
Thermal Resistance, Junction to Ambient (Note 4) @ T _A = 25°C	$R_{ ext{ heta}JA}$	250	°C/W
Operating and Storage Temperature Range	TJ, T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Conditions	
OFF CHARACTERISTICS					•		
Collector-Base Breakdown Voltage	V _{(BR)CBO}	15	_	_	V	$I_{C} = 10 \mu A, I_{E} = 0$	
Collector-Emitter Breakdown Voltage (Note 5)	V _{(BR)CEO}	12	_	_	V	$I_{\rm C} = 1 {\rm mA}, I_{\rm B} = 0$	
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	6	_	_	V	$I_{\rm E} = 10 \mu A, I_{\rm C} = 0$	
Collector Cut-Off Current	I _{CBO}	_	_	0.1	μΑ	$V_{CB} = 15V, I_E = 0$	
Emitter Cut-Off Current	I _{EBO}	_	_	0.1	μΑ	$V_{EB} = 6V, I_{C} = 0$	
ON CHARACTERISTICS (Note 5)							
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	80	200	mV	$I_{C} = 500 \text{mA}, I_{B} = 25 \text{mA}$	
DC Current Gain	h _{FE}	270	_	680		$V_{CE} = 2V, I_{C} = 200 \text{mA}$	
SMALL SIGNAL CHARACTERISTICS							
Output Capacitance	C _{obo}		11	_	pF	$V_{CB} = 10V, I_E = 0,$ f = 1MHz	
Current Gain-Bandwidth Product	f _T	_	260	_	MHz	$V_{CE} = 2V, I_C = 100$ mA, f = 100MHz	

Notes: 1. No purposefully added lead.

2. Diode's Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

- 4. Device mounted on FR-4 PCB with 1 inch² copper pad layout.
- 5. Measured under pulsed conditions. Pulse width = $300\mu s$. Duty cycle $\leq 2\%$.

Device mounted on FR-4 PCB with minimum recommended pad layout.



0.6

0.5

0.4

0.3

0.2

0.1

0

1,000

h_{FE}, DC CURRENT GAIN

100

10

1.2

1.0

0.8

0.6

0.4

0.2

0

0.1

Fig. 5 Typical Base-Emitter Turn-On Voltage

vs. Collector Current

T,

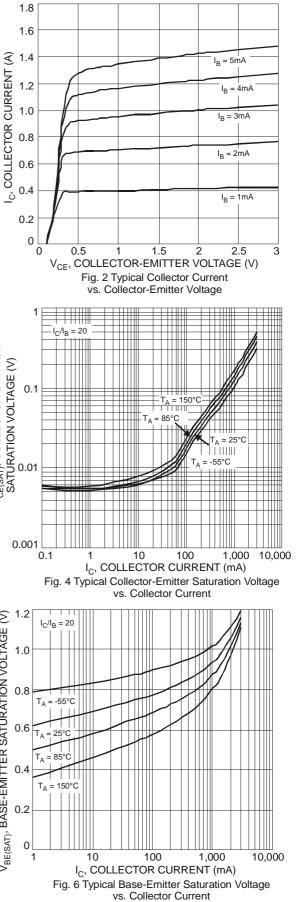
V_{BE(ON)}, BASE-EMITTER TURN-ON VOLTAGE (V)

0.1

0

P_D, POWER DISSIPATION (W)

1.8 1.6 I_C, COLLECTOR CURRENT (A) 1.4 1.2 1.0 (Note 4) 0.8 (Note 3) 0.6 0.4 0.2 0 0 150 175 200 25 50 75 100 125 T_A, AMBIENT TEMPERATURE (°C) Fig. 1 Power Dissipation vs. Ambient Temperature 1 = 150°C V_{CE(SAT)}, COLLECTOR-EMITTER SATURATION VOLTAGE (V) 10 10 10 85°C = 25°C = -55°C V_{CE} = 2V 0.001 10 100 1,000 10,000 0.1 1 I_C, COLLECTOR CURRENT (mA) Fig. 3 Typical DC Current Gain vs. Collector Current V_{BE(SAT}), BASE-EMITTER SATURATION VOLTAGE (V) 1.2 $V_{CE} = 2V$ 1.0 0.8 -55°C 0.6 25°C 500 85°C 0.4 85°C T۵ 0.2 150°C 0 10 100 1,000 COLLECTOR CURRENT (mA) 10,000 1 1 I_C,



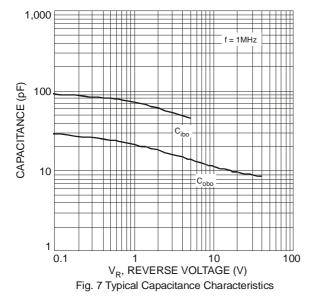
NEW PRODUCT

2DD2652 Document number: DS31633 Rev. 2 - 2 Downloaded from Arrow.com.

2DD2652



2DD2652



Ordering Information (Note 6)

Part Number	Case	Packaging
2DD2652-7	SOT-323	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

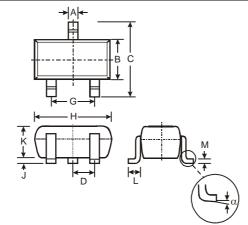


RN2 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: V = 2008) M = Month (ex: 9 = September)

Date Code Key

Year	2008		2009	2010		2011	2012		2013	2014		2015
Code	V		W	Х		Y	Z		А	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Package Outline Dimensions

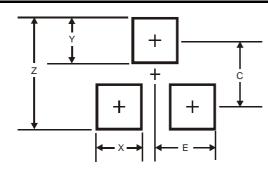


SOT-323					
Dim	Min	Max	Тур		
Α	0.25	0.40	0.30		
В	1.15	1.35	1.30		
С	2.00	2.20	2.10		
D	-	-	0.65		
G	1.20	1.40	1.30		
н	1.80	2.20	2.15		
J	0.0	0.10	0.05		
ĸ	0.90	1.00	1.00		
L	0.25	0.40	0.30		
М	0.10	0.18	0.11		
α	0°	8°	-		
All	All Dimensions in mm				



2DD2652

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.8
Х	0.7
Y	0.9
С	1.9
E	1.0

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